

Title (en)

Process for manufacturing thick suspended structures of semiconductor material

Title (de)

Verfahren zum Herstellen von dicken hängenden Strukturen aus Halbleitermaterial

Title (fr)

Procédé pour réaliser des structures suspendues épaisses en matériau semiconducteur

Publication

EP 1770055 B1 20080528 (EN)

Application

EP 05425676 A 20050928

Priority

EP 05425676 A 20050928

Abstract (en)

[origin: EP1770055A1] A process for manufacturing a suspended structure (20) of semiconductor material envisages the steps of: providing a monolithic body (10) of semiconductor material having a front face (10a); forming a buried cavity (17) within the monolithic body (10), extending at a distance from the front face (10a) and delimiting, with the front face (10a), a surface region (18) of the monolithic body (10), said surface region (18) having a first thickness (w_1); carrying out a thickening thermal treatment such as to cause a migration of semiconductor material of the monolithic body (10) towards the surface region (18) and thus form a suspended structure (20) above the buried cavity (17), the suspended structure (20) having a second thickness (w_2) greater than the first thickness (w_1). The thickening thermal treatment is an annealing treatment.

IPC 8 full level

B81B 3/00 (2006.01)

CPC (source: EP US)

B81C 1/00158 (2013.01 - EP US); **B81B 2201/025** (2013.01 - EP US); **B81B 2203/0109** (2013.01 - EP US); **B81B 2203/0315** (2013.01 - EP US); **B81C 2201/0116** (2013.01 - EP)

Designated contracting state (EPC)

DE FR GB IT

DOCDB simple family (publication)

EP 1770055 A1 20070404; **EP 1770055 B1 20080528**; DE 602005007235 D1 20080710; US 2007126071 A1 20070607; US 7871894 B2 20110118

DOCDB simple family (application)

EP 05425676 A 20050928; DE 602005007235 T 20050928; US 54137606 A 20060927